

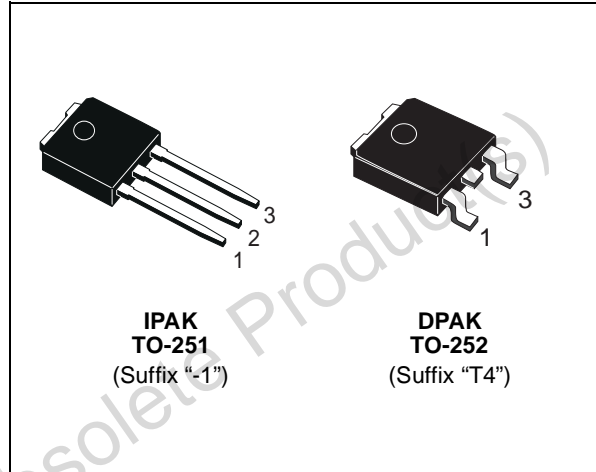


# STD10PF06

## P-CHANNEL 60V - 0.18 $\Omega$ - 10A IPAK/DPAK STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD10PF06	60 V	< 0.20 $\Omega$	10 A

- TYPICAL R<sub>DS(on)</sub> = 0.18  $\Omega$
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")



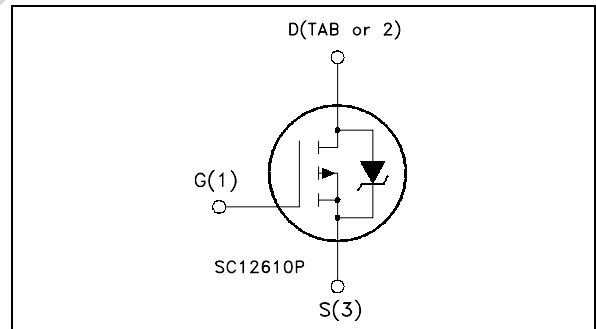
### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

- MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	60	V
V <sub>GS</sub>	Gate- source Voltage	$\pm 20$	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	10	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	7	A
I <sub>DM</sub> (*)	Drain Current (pulsed)	40	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C	40	W
	Derating Factor	0.27	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	6	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(\*) Pulse width limited by safe operating area.  
Note: P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

(1) I<sub>SD</sub>  $\leq$  10A, di/dt  $\leq$  300A/ $\mu$ s, V<sub>DD</sub>  $\leq$  V<sub>(BR)DSS</sub>, T<sub>j</sub>  $\leq$  T<sub>JMAX</sub>

**STD10PF06****THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case	Max	3.75	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	100	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		275	°C

**AVALANCHE CHARACTERISTICS**

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	10	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	125	mJ

**ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED)**  
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±1	μA

## ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2		4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 5 A		0.18	0.20	Ω

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 25 V I <sub>D</sub> = 5 A	2	5		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		850 230 75		pF pF pF

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## ELECTRICAL CHARACTERISTICS (continued)

### SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		20 40		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48\text{ V}$ $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$		16 4 6	21	nC nC nC

### SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 30\text{ V}$ $I_D = 5\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		40 10		ns ns
$t_r(V_{off})$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{clamp} = 48\text{ V}$ $I_D = 10\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (Inductive Load, Figure 5)		10 17 30		ns ns ns

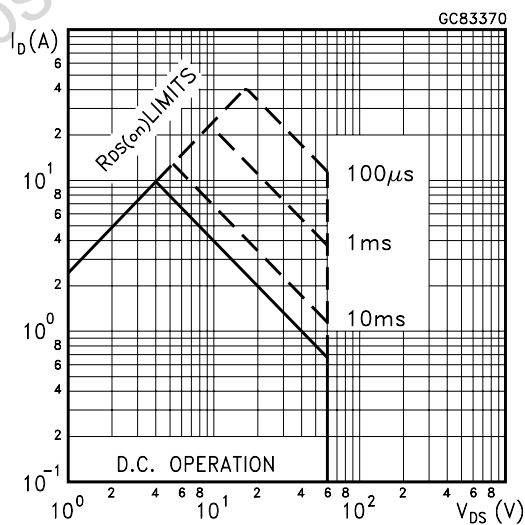
### SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				10 40	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 10\text{ A}$ $V_{GS} = 0$			2.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 10\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		100 260 5.2		ns $\mu\text{C}$ A

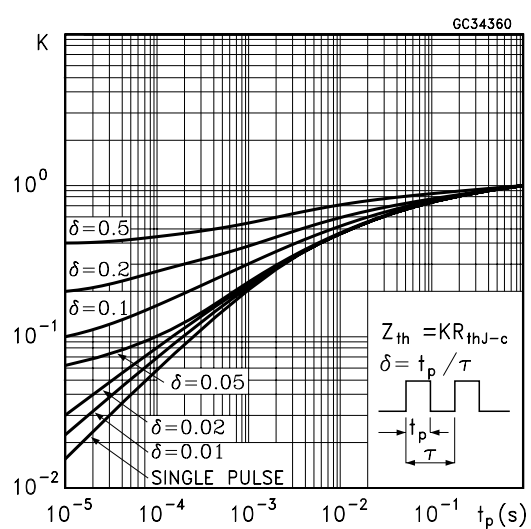
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

( $\bullet$ ) Pulse width limited by safe operating area.

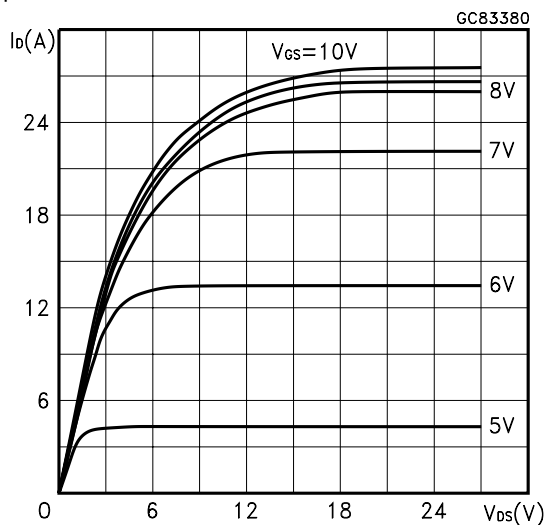
### Safe Operating Area



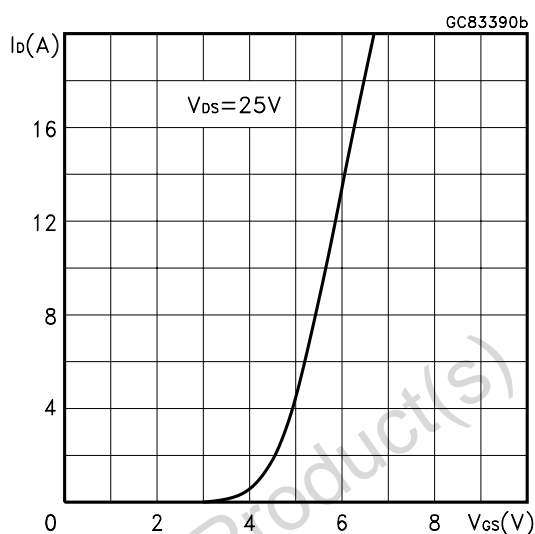
### Thermal Impedance



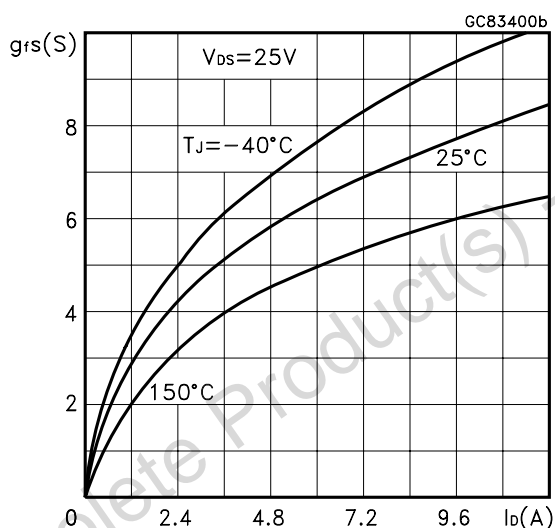
Output Characteristics



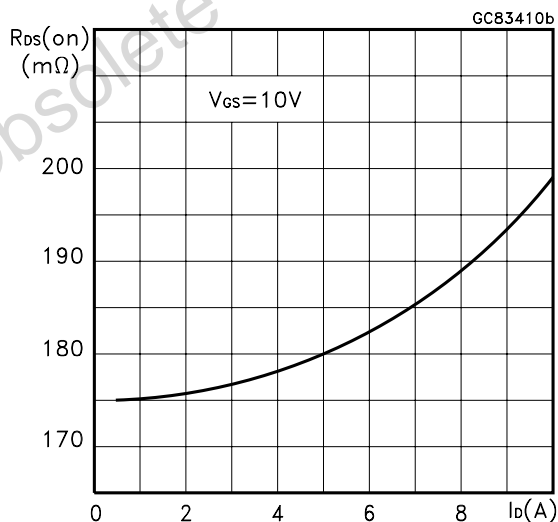
Transfer Characteristics



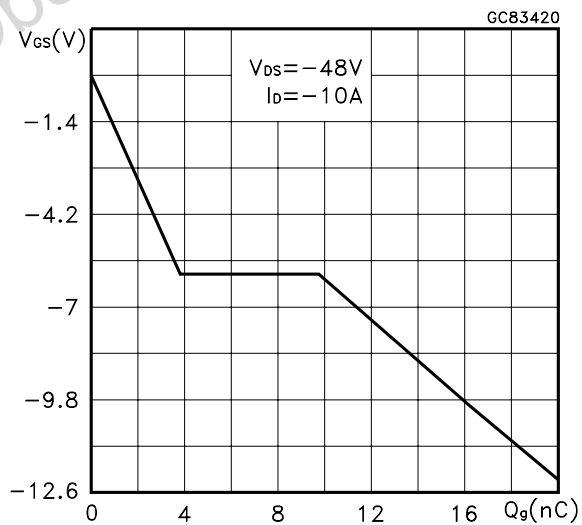
Transconductance



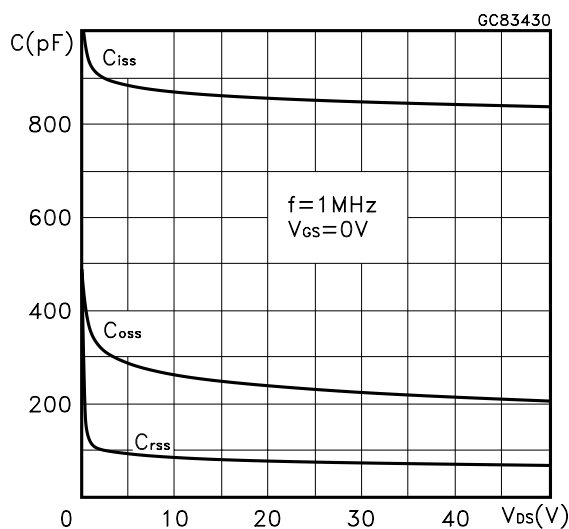
Static Drain-source On Resistance



Gate Charge vs Gate-source Voltage

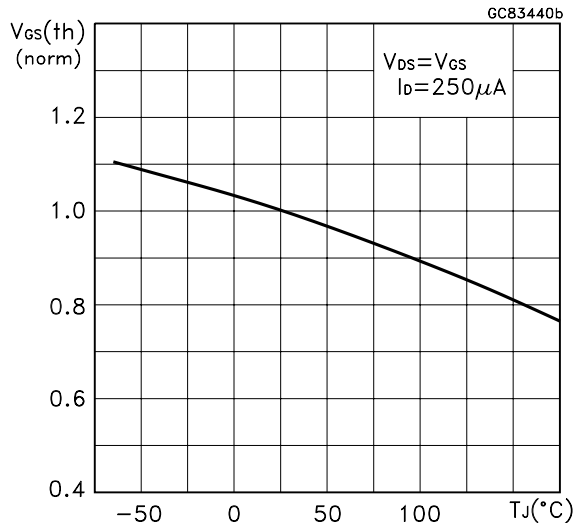


Capacitance Variations

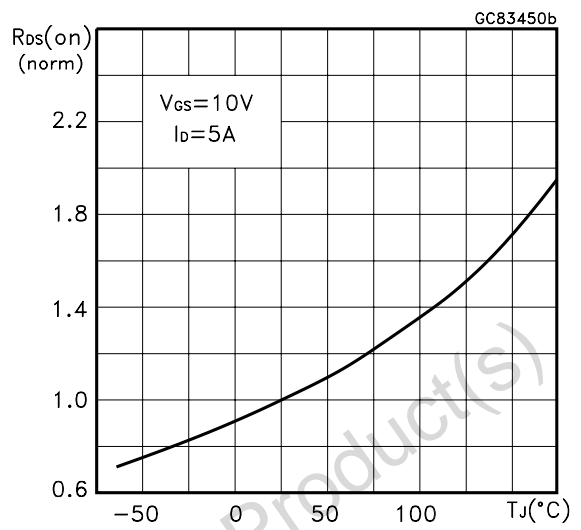


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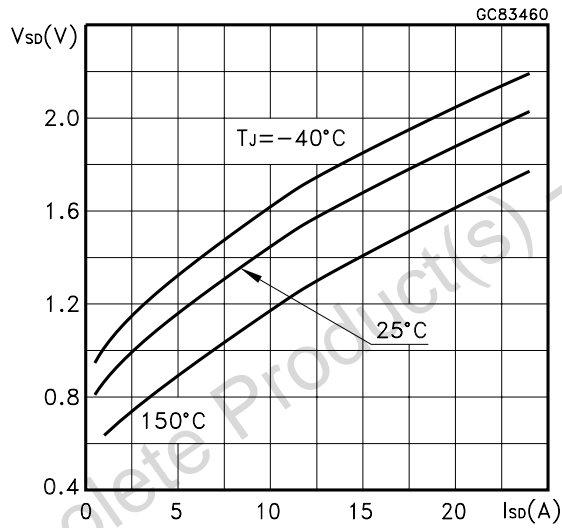
Normalized Gate Threshold Voltage vs Temperature



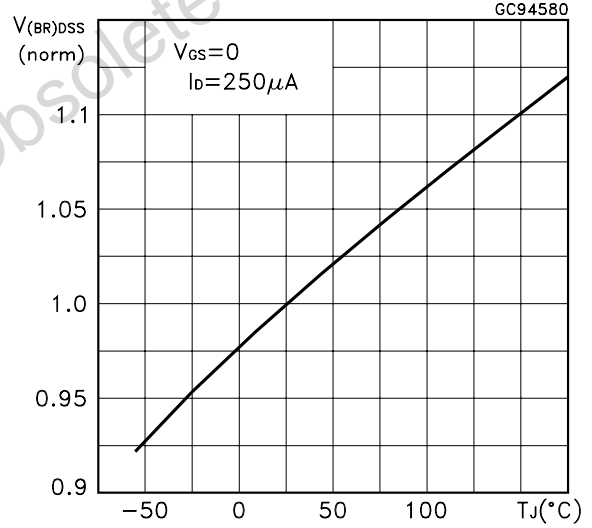
Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



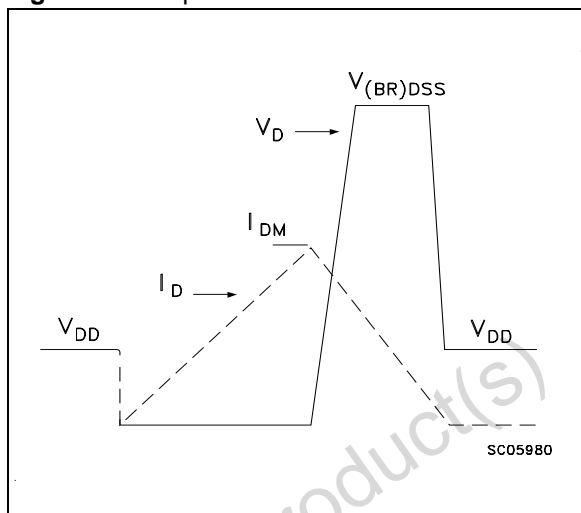
Normalized Breakdown Voltage Temperature



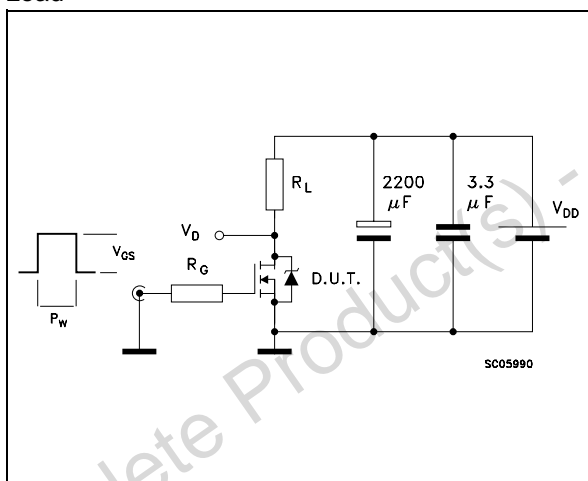
**Fig. 1: Unclamped Inductive Load Test Circuit**



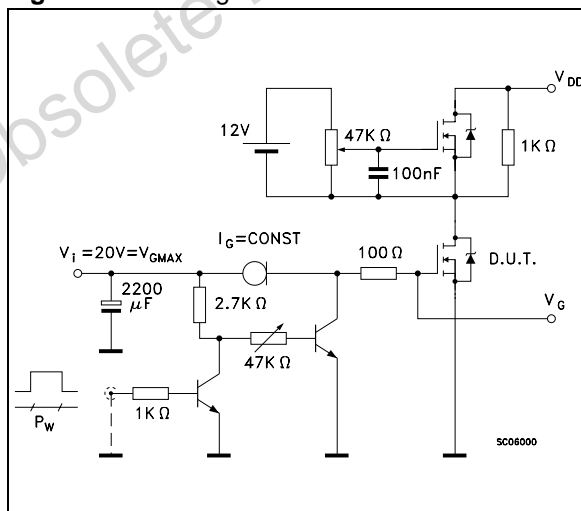
**Fig. 2: Unclamped Inductive Waveform**



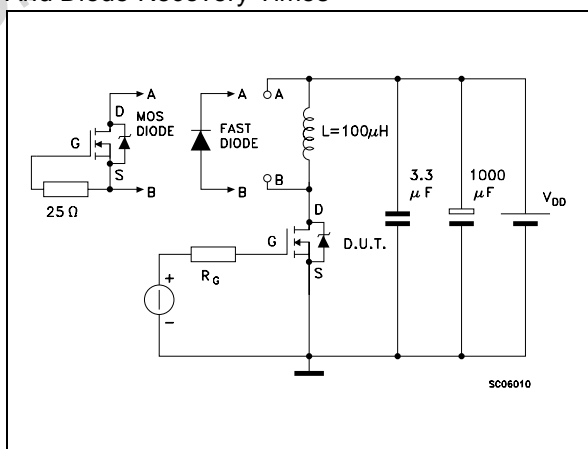
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

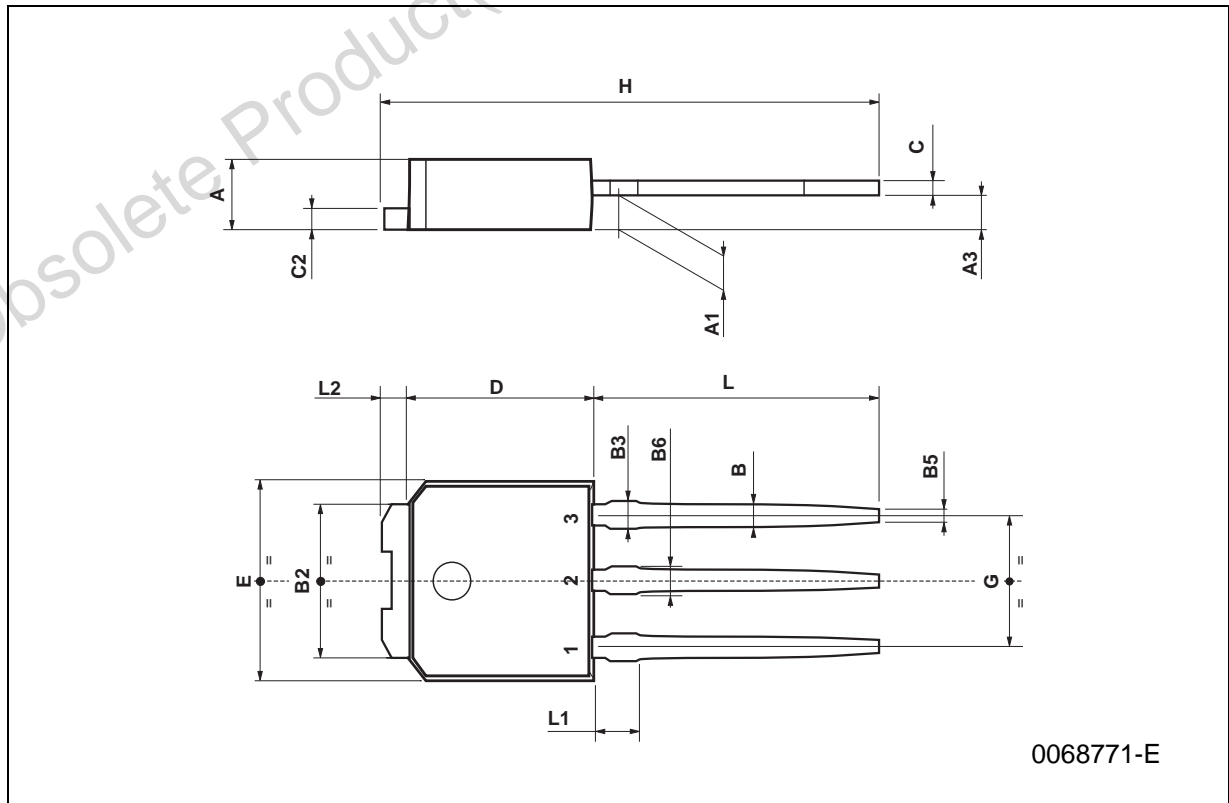


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



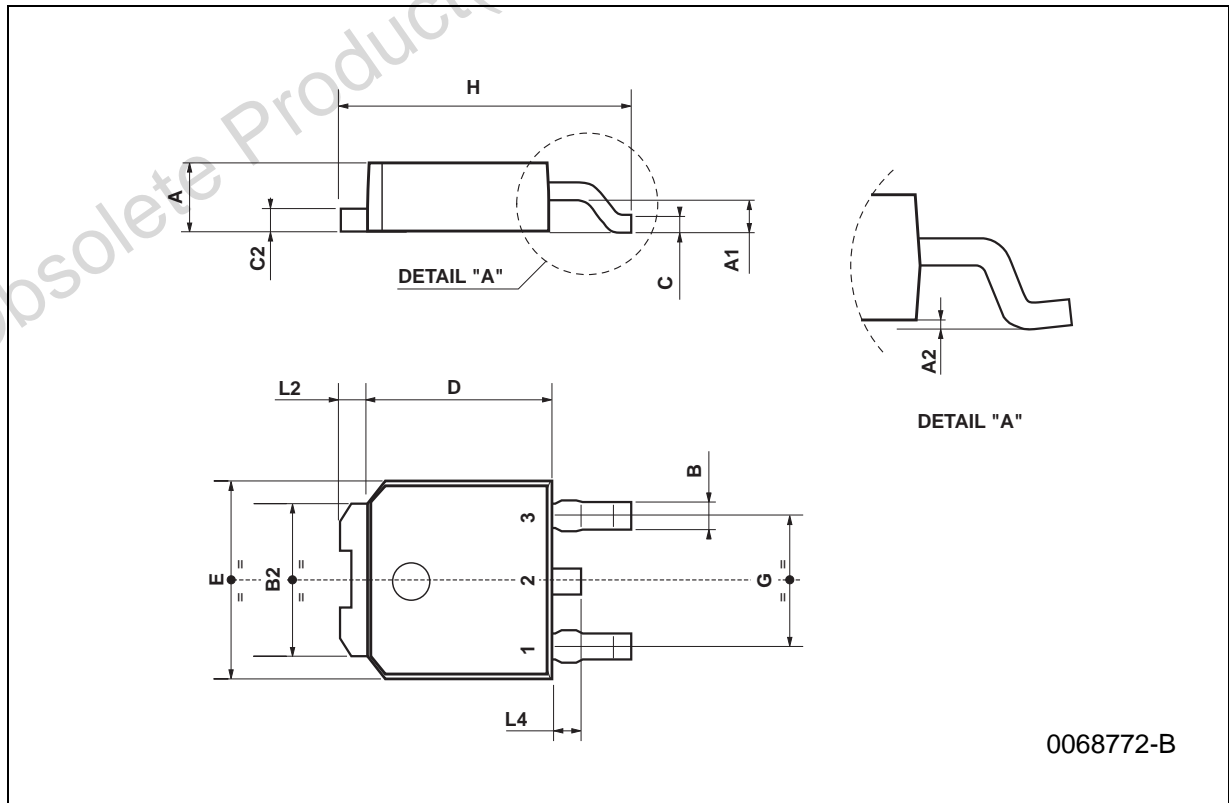
**TO-251 (IPAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



**TO-252 (DPAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039





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